Walter R L Lambrecht

List of Publications by Year in Descending Order

265 papers	11,620 citations	54 h-index	99 g-index
281 ext. papers	12,575 ext. citations	3.6 avg, IF	6.69 L-index

#	Paper	IF	Citations
265	N2, NO, and O2 molecules in LiGaO2 in both Ga and Li sites and their relation to the vacancies. *Journal of Applied Physics*, **2022**, 131, 145705	2.5	0
264	Spin-polarized two-dimensional electron/hole gases on LiCoO$_2$ layers.. *SciPost Physics*, **2021**, 10,	6.1	2
263	Experimental determination of the valence band offsets of ZnGeN2 and (ZnGe)0.94Ga0.12N2 with GaN. *Journal Physics D: Applied Physics*, **2021**, 54, 245102	3	2
262	Ultrathin 2D-oxides: A perspective on fabrication, structure, defect, transport, electron, and phonon properties. *Journal of Applied Physics*, **2021**, 129, 220903	2.5	4
261	Electron microscopy and spectroscopic study of structural changes, electronic properties, and conductivity in annealed LixCoO2. *Physical Review Materials*, **2021**, 5,	3.2	3
260	Calculated phonon modes, infrared and Raman spectra in orthorhombic □MoO3 and monolayer MoO3. *Journal of Applied Physics*, **2021**, 130, 104302	2.5	
259	Optical response and band structure of LiCoO2 including electron-hole interaction effects. *Physical Review B*, **2021**, 104,	3.3	3
258	Quasiparticle self-consistent GW band structures and high-pressure phase transitions of LiGaO2 and NaGaO2. *Physical Review B*, **2021**, 103,	3.3	3
257	Topological quantum switch and controllable one-dimensional conducting paths in antimonene facilitated by breaking the inversion symmetry. *Physical Review B*, **2020**, 102,	3.3	1
256	First-principles study of n- and p-type doping opportunities in LiGaO2. *Journal Physics D: Applied Physics*, **2020**, 53, 274002	3	6
255	Topological band structure transitions and goniopolar transport in honeycomb antimonene as a function of buckling. *Physical Review B*, **2020**, 101,	3.3	6
254	Deep level defects and cation sublattice disorder in ZnGeN2. *Journal of Applied Physics*, **2020**, 127, 135703	2.5	12
253	First-principles study of the phonon replicas in the photoluminescence spectrum of 4H-SiC. *Physical Review B*, **2020**, 101,	3.3	1
252	Candidates for p-type doping of ZnGeN2. *Journal of Applied Physics*, **2020**, 127, 075707	2.5	4
251	Quasiparticle self-consistent GW band structure of CrN. *Physical Review B*, **2020**, 101,	3.3	4
250	Computational study of electron paramagnetic resonance spectra for Li and Ga vacancies in LiGaO2. *Journal Physics D: Applied Physics*, **2020**, 53, 17LT01	3	1
249	Quasiparticle self-consistent GW energy band calculations for Ge3N4 phases. *Physical Review B*, **2020**, 102,	3.3	2

248	Band alignment of III-N, ZnO and II-IV-N2 semiconductors from the electron affinity rule. *Journal Physics D: Applied Physics*, **2020**, 53, 015111	3	6
247	Understanding the Crystallographic Phase Relations in Alkali-Trihalogeno-Germanates in Terms of Ferroelectric or Antiferroelectric Arrangements of the Tetrahedral GeX3 Units. *Advanced Electronic Materials*, **2020**, 6, 1900887	6.4	0
246	Metal-Organic Chemical Vapor Deposition of ZnGeGa2N4. *Crystal Growth and Design*, **2020**, 20, 189-196	3.5	4
245	Effects of the van der Waals Interactions on Structural and Electronic Properties of CHNH(Pb,Sn)(I,Br,Cl) Halide Perovskites. *ACS Omega*, **2020**, 5, 25723-25732	3.9	4
244	Buckled honeycomb antimony: Higher order topological insulator and its relation to the Kekulé lattice. *Physical Review B*, **2020**, 102,	3.3	6
243	Electrical Characterization and Charge Transport in Chemically Exfoliated 2D LixCoO2 Nanoflakes. *Journal of Physical Chemistry C*, **2020**, 124, 20693-20700	3.8	6
242	Calculated phonon modes, infrared, and Raman spectra in ZnGeGa2N4. *Journal of Applied Physics*, **2020**, 128, 075702	2.5	0
241	Quasiparticle Self-Consistent GW Study of (Ga1-xAlx)2O3 Alloys in Monoclinic and Corundum Structures. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 1900317	1.3	4
240	Proton irradiation induced defects in β-Ga2O3: A combined EPR and theory study. *APL Materials*, **2019**, 7, 022521	5.7	33
239	Computational identification of Ga-vacancy related electron paramagnetic resonance centers in β-Ga2O3. *Journal of Applied Physics*, **2019**, 125, 185701	2.5	22
238	Computational study of electron paramagnetic resonance parameters for Mg and Zn impurities in β-Ga2O3. *Applied Physics Letters*, **2019**, 114, 202102	3.4	12
237	Quasiparticle self-consistent GW electronic band structures of Be-IV-N compounds. *Journal of Physics Condensed Matter*, **2019**, 31, 335501	1.8	2
236	Band Gaps, Band-Offsets, Disorder, Stability Region, and Point Defects in II-IV-N2 Semiconductors. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1800875	1.6	16
235	Band Gaps and Stability of CsSiX3 Halides. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1800962	1.6	2
234	First-principles calculations of phonon derived Raman and infrared spectra in Be-IV-N2 compounds. *Journal Physics D: Applied Physics*, **2019**, 52, 385106	3	2
233	First-principles study of point defects in LiGaO2. *Journal of Applied Physics*, **2019**, 126, 155703	2.5	8
232	Instability of the layered orthorhombic post-perovskite phase of SrTiO3 and other candidate orthorhombic phases under pressure. *Solid State Communications*, **2018**, 274, 27-30	1.6	3
231	Role of the different defects, their population and distribution in the LaAlO3/SrTiO3 heterostructure's behavior. *Journal of Applied Physics*, **2018**, 123, 155304	2.5	6

230	Ion blocking dip shape analysis around a LaAlO3/SrTiO3 interface. *Nuclear Instruments & Methods in Physics Research B*, **2018**, 423, 67-71	1.2	2
229	First-principles calculations of elastic and piezoelectric constants and spontaneous polarization in Cd-IV-N2 compounds. *Journal of Applied Physics*, **2018**, 124, 055705	2.5	2
228	All-electron quasiparticle self-consistent GW band structures for SrTiO3 including lattice polarization corrections in different phases. *Physical Review Materials*, **2018**, 2,	3.2	21
227	Distortion modes in halide perovskites: To twist or to stretch, a matter of tolerance and lone pairs. *Physical Review Materials*, **2018**, 2,	3.2	15
226	Ordering in the mixed ZnGeN2-GaN alloy system: Crystal structures and band structures of ZnGeGa2N4 from first principles. *Physical Review Materials*, **2018**, 2,	3.2	9
225	First-principles calculations of second-order nonlinear optical coefficients in the static limit and Pockels coefficients in III-N and II-IV-N2 compounds. *Physical Review Materials*, **2018**, 2,	3.2	2
224	Optoelectronic Dichotomy of Mixed Halide CHNHPb(BrCl) Single Crystals: Surface versus Bulk Photoluminescence. *Journal of the American Chemical Society*, **2018**, 140, 11811-11819	16.4	18
223	First-principles calculations of phonons and Raman and infrared spectra in Cd-IV-N2 compounds. *Journal of Applied Physics*, **2018**, 123, 205701	2.5	7
222	Core-level binding energy shifts as a tool to study surface processes on LaAlO 3 /SrTiO 3. *Journal of Electron Spectroscopy and Related Phenomena*, **2017**, 218, 21-29	1.7	12
221	Quasiparticle self-consistent GW band structure of Ga2O3 and the anisotropy of the absorption onset. *Applied Physics Letters*, **2017**, 110, 132103	3.4	22
220	Raman study of the vibrational modes in ZnGeN2 (0001). *Journal of Applied Physics*, **2017**, 121, 055704	2.5	9
219	Carrier-controlled anomalous Hall effect in an intrinsic ferromagnetic semiconductor. *Physical Review B*, **2017**, 96,	3.3	12
218	VO: A 2D van der Waals Oxide with Strong In-Plane Electrical and Optical Anisotropy. *ACS Applied Materials & Interfaces*, **2017**, 9, 23949-23956	9.5	23
217	Zone-center phonons in yellow phase CsSnI3. *Physical Review Materials*, **2017**, 1,	3.2	2
216	Quasiparticle self-consistent GW electronic band structure of Cd-IV-N2 compounds. *Physical Review Materials*, **2017**, 1,	3.2	12
215	Lattice polarization effects on the screened Coulomb interaction W of the GW approximation. *Physical Review Materials*, **2017**, 1,	3.2	25
214	Native interstitial defects in ZnGeN2. *Physical Review Materials*, **2017**, 1,	3.2	7
213	Vibrational spectra and nonlinear optical coefficients of rhombohedral CsGeX3 halide compounds with X=I, Br, Cl. *Physical Review B*, **2016**, 94,	3.3	11

212	Electronic band structure of MgGeN2 compounds in the quasiparticle-self-consistent GW approximation. *Physical Review B*, **2016**, 94,	3.3	39
211	Native point defects and doping in ZnGeN2. *Physical Review B*, **2016**, 93,	3.3	38
210	Electronic band structure trends of perovskite halides: Beyond Pb and Sn to Ge and Si. *Physical Review B*, **2016**, 93,	3.3	86
209	Disorder effects on the band structure of ZnGeN2: Role of exchange defects. *Physical Review B*, **2016**, 94,	3.3	31
208	Atomic-resolved depth profile of strain and cation intermixing around LaAlO3/SrTiO3 interfaces. *Scientific Reports*, **2016**, 6, 28118	4.9	22
207	Vibrational modes in the Pmc21 structure of ZnGeN2. *Solid State Communications*, **2016**, 233, 46-49	1.6	6
206	First-principles calculations of phonons and Raman spectra in monoclinic CsSnCl3. *Physical Review B* , **2015**, 91,	3.3	9
205	Charge-neutral disorder and polytypes in heterovalent wurtzite-based ternary semiconductors: The importance of the octet rule. *Physical Review B*, **2015**, 91,	3.3	76
204	Fully opposite spin polarization of electron and hole bands in DyN and related band structures of GdN and HoN. *Physical Review B*, **2015**, 92,	3.3	3
203	Systematic study of the exchange interactions in Gd-doped GaN containing N interstitials, O interstitials, or Ga vacancies. *Physical Review B*, **2015**, 92,	3.3	14
202	Electronic and magnetic properties of electron-doped V2O5 and NaV2O5. *Physical Review B*, **2015**, 92,	3.3	5
201	Effects of structural relaxation, interdiffusion, and surface termination on two-dimensional electron gas formation at the LaAlO3/SrTiO3 (001) interface. *Physical Review B*, **2015**, 92,	3.3	16
200	Quasiparticle self-consistent GW calculations of the electronic band structure of bulk and monolayer V2O5. *Physical Review B*, **2015**, 91,	3.3	33
199	Theory of light emission polarization reversal in zinc-blende and wurtzite nanowires. *Physical Review B*, **2014**, 89,	3.3	7
198	Phonons and related spectra in bulk and monolayer V2O5. *Physical Review B*, **2014**, 89,	3.3	22
197	Lattice dynamics in perovskite halides CsSnX3 with X=I, Br, Cl. *Physical Review B*, **2014**, 90,	3.3	54
196	Band offsets between ZnGeN2, GaN, ZnO, and ZnSnN2 and their potential impact for solar cells. *Physical Review B*, **2013**, 88,	3.3	72
195	Strain effects on the spin-orbit-induced band structure splittings in monolayer MoS2 and graphene. *Physical Review B*, **2013**, 88,	3.3	40

194	Electronic band structure, phonons, and exciton binding energies of halide perovskites CsSnCl3, CsSnBr3, and CsSnI3. *Physical Review B*, **2013**, 88,	3.3	312
193	Electronic structure of defects and doping in ZnO: Oxygen vacancy and nitrogen doping. *Physica Status Solidi (B): Basic Research*, **2013**, 250, 2091-2101	1.3	16
192	Rare-earth mononitrides. *Progress in Materials Science*, **2013**, 58, 1316-1360	42.2	93
191	Identification of a N-related shallow acceptor and electron paramagnetic resonance center in ZnO: N2+ on the Zn site. *Physical Review B*, **2013**, 87,	3.3	27
190	Electronic structure of defects and doping in ZnO: Oxygen vacancy and nitrogen doping. *Physica Status Solidi (B): Basic Research*, **2013**, 250, n/a-n/a	1.3	18
189	Heterovalent ternary II-IV-N2 compounds: perspectives for a new class of wide-band-gap nitrides **2013**, 519-585		14
188	Valence band effective-mass Hamiltonians for the group-III nitrides from quasiparticle self-consistent GW band structures. *Physical Review B*, **2012**, 85,	3.3	35
187	Electronic band structure of graphene from resonant soft x-ray spectroscopy: The role of core-hole effects. *Physical Review B*, **2012**, 86,	3.3	25
186	Quasiparticle band structure calculation of monolayer, bilayer, and bulk MoS2. *Physical Review B*, **2012**, 85,	3.3	980
185	GaAs Nanowires: A New Place to Explore Polytype Physics. *Materials Science Forum*, **2012**, 717-720, 565-568	0.4	1
184	Valence band structure of polytypic zinc-blende/wurtzite GaAs nanowires probed by polarization-dependent photoluminescence. *Physical Review B*, **2012**, 85,	3.3	53
183	Nitrogen pair□ydrogen complexes in ZnO and p-type doping.. *Materials Research Society Symposia Proceedings*, **2012**, 1394, 27		4
182	Superparamagnetism in Gd-doped GaN induced by Ga-vacancy clustering. *Physical Review B*, **2012**, 86,	3.3	22
181	Single well or double well: First-principles study of 8H and 3C inclusions in the 4H SiC polytype. *Physical Review B*, **2012**, 85,	3.3	3
180	CdGeN2 and ZnGe0.5Sn0.5N2: Two New Nitride Semiconductors with Band Gaps in the Blue-Green. *Materials Science Forum*, **2012**, 717-720, 1331-1334	0.4	4
179	First-principles calculation of resonant x-ray emission spectra applied to ZnO. *Physical Review B*, **2011**, 83,	3.3	5
178	Band structure parameters of wurtzite and zinc-blende GaAs under strain in the GW approximation. *Physical Review B*, **2011**, 84,	3.3	58
177	Critical Evaluation of the LDA + U Approach for Band Gap Corrections in Point Defect Calculations: The Oxygen Vacancy in ZnO Case Study **2011**, 165-181		

176	Which Electronic Structure Method for The Study of Defects: A Commentary **2011**, 359-379		
175	Which electronic structure method for the study of defects: A commentary. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 1547-1558	1.3	35
174	Critical evaluation of the LDA + U approach for band gap corrections in point defect calculations: The oxygen vacancy in ZnO case study. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 1043-1051	1.3	24
173	Electronic and lattice dynamical properties of II-IV-N2 semiconductors. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2492-2499		45
172	Quasiparticle band structure of Zn-IV-N2 compounds. *Physical Review B*, **2011**, 84,	3.3	109
171	Calculated x-ray linear dichroism spectra for Gd-doped GaN. *Physical Review B*, **2011**, 84,	3.3	1
170	Electronic structure of EuN: Growth, spectroscopy, and theory. *Physical Review B*, **2011**, 84,	3.3	31
169	Site Dependence of Electronic Structure of Gd Impurities in GaN. *Materials Research Society Symposia Proceedings*, **2011**, 1290, 1		2
168	First-principles Study of Nitrogen Vacancies in GdN. *Materials Research Society Symposia Proceedings*, **2011**, 1290, 1		19
167	Electronic structure, doping, and lattice dynamics of LiGaO 2 **2011**,		5
166	Pressure-dependent elastic constants and sound velocities of wurtzite SiC, GaN, InN, ZnO, and CdSe, and their relation to the high-pressure phase transition: A first-principles study. *Physical Review B*, **2010**, 82,	3.3	78
165	Electronic band structure information of GdN extracted from x-ray absorption and emission spectroscopy. *Applied Physics Letters*, **2010**, 96, 032101	3.4	18
164	First-principles study of the elasticity, piezoelectricity, and vibrational modes in LiGaO2 compared with ZnO and GaN. *Physical Review B*, **2010**, 81,	3.3	33
163	First-principles study of oxygen vacancies in MgxZn1−xO alloys. *Physical Review B*, **2010**, 81,	3.3	12
162	Interstitial-nitrogen- and oxygen-induced magnetism in Gd-doped GaN. *Physical Review B*, **2009**, 80,	3.3	59
161	First-principles calculations of elasticity, polarization-related properties, and nonlinear optical coefficients in Zn-IV-N2 compounds. *Physical Review B*, **2009**, 79,	3.3	61
160	Computational study of phonon modes in short-period AlN/GaN superlattices. *Physical Review B*, **2009**, 80,	3.3	12
159	Vibrational properties of rare-earth nitrides: Raman spectra and theory. *Physical Review B*, **2009**, 79,	3.3	21

158	Bond lengths, phase stability, and band gaps in MgxZn1−xO alloys. *Journal of Vacuum Science & Technology B*, **2009**, 27, 1717		3
157	Calculated phonon band structure and density of states and interpretation of the Raman spectrum in rocksalt ScN. *Physical Review B*, **2009**, 79,	3.3	31
156	Electronic structure of CrN: A borderline Mott insulator. *Physical Review B*, **2009**, 79,	3.3	62
155	Jahn–Teller Distortion of the Zinc Vacancy in ZnGeP 2. *Chinese Physics Letters*, **2008**, 25, 1075-1078	1.8	2
154	Calculated interband optical transition spectra of GdN. *Physical Review B*, **2008**, 78,	3.3	19
153	Vibrational modes in ZnGeN2: Raman study and theory. *Physical Review B*, **2008**, 77,	3.3	34
152	First-principles study of phonons and related ground-state properties and spectra in Zn-IV-N2 compounds. *Physical Review B*, **2008**, 78,	3.3	61
151	Linear response theoretical study of the exchange interactions in Mn-doped ScN: Effects of disorder, band gap, and doping. *Physical Review B*, **2008**, 77,	3.3	15
150	Magnetic exchange interactions in the gadolinium pnictides from first principles. *Physical Review B*, **2008**, 78,	3.3	35
149	First-principles calculation of the O vacancy in ZnO: A self-consistent gap-corrected approach. *Physical Review B*, **2008**, 77,	3.3	123
148	First-principles study of native defects in CdGeAs2. *Physical Review B*, **2008**, 78,	3.3	10
147	Electronic structure and magnetism in Bi2Te3, Bi2Se3, and Sb2Te3 doped with transition metals (Ti–Zn). *Physical Review B*, **2008**, 78,	3.3	53
146	Effects of vacancies and impurities on the relative stability of rocksalt and zincblende structures for MnN. *Physical Review B*, **2007**, 76,	3.3	9
145	Electronic and crystal structure of Cu2−xS: Full-potential electronic structure calculations. *Physical Review B*, **2007**, 76,	3.3	202
144	Electronic structure of 3C inclusions in 4H SiC. *Journal of Applied Physics*, **2007**, 101, 103711	2.5	20
143	First-principles calculation of the zone center phonons in ZnSiN2: Comparison with infrared data. *Physical Review B*, **2007**, 76,	3.3	21
142	Comparison between experiment and calculated band structures for DyN and SmN. *Physical Review B*, **2007**, 76,	3.3	40
141	Ferromagnetic redshift of the optical gap in GdN. *Physical Review B*, **2007**, 76,	3.3	67

140	Large band-gap bowing in Cu1−xAgxGaS2 chalcopyrite semiconductors and its effect on optical parameters. *Physical Review B*, **2007**, 76,	3.3	4
139	Electronic structure of rare-earth nitrides using the LSDA+U approach: Importance of allowing 4f orbitals to break the cubic crystal symmetry. *Physical Review B*, **2007**, 75,	3.3	270
138	Band-gap bowing in AgGa(Se1−xTex)2 and its effect on the second-order response coefficient and refractive indices. *Physical Review B*, **2007**, 76,	3.3	6
137	Stacking Faults and 3C Quantum Wells in Hexagonal SiC Polytypes. *Materials Science Forum*, **2006**, 527-529, 351-354	0.4	2
136	Gadolinium and Oxygen co-doping of Gallium Nitride: an LSDA + U study. *Materials Research Society Symposia Proceedings*, **2006**, 955, 1		
135	Electronic structure and magnetic properties of transition-metal-doped 3C and 4H silicon carbide. *Physical Review B*, **2006**, 74,	3.3	45
134	Electronic structure of Gd pnictides calculated within the LSDA+U approach. *Physical Review B*, **2006**, 74,	3.3	52
133	Theoretical study of the phosphorus vacancy in ZnGeP2. *Physical Review B*, **2006**, 73,	3.3	16
132	Electronic driving force for stacking fault expansion in 4H-SiC. *Physical Review B*, **2006**, 73,	3.3	49
131	Electronic structure and magnetism of europium chalcogenides in comparison with gadolinium nitride. *Journal of Physics Condensed Matter*, **2006**, 18, 11333-11345	1.8	40
130	Electronic Structure and Magnetic Properties of Transition Metal Doped Silicon Carbide in Different Polytypes. *Materials Science Forum*, **2006**, 527-529, 641-646	0.4	1
129	Mn-doped ScN: A dilute ferromagnetic semiconductor with local exchange coupling. *Physical Review B*, **2005**, 72,	3.3	41
128	Magnetic properties of transition-metal nitrides. *Journal of Applied Physics*, **2005**, 97, 10D306	2.5	31
127	Structure and magnetic properties of MnN, CrN, and VN under volume expansion. *Physical Review B* , **2005**, 71,	3.3	28
126	Optical conductivity and x-ray absorption and emission study of the band structure of MnN films. *Physical Review B*, **2005**, 72,	3.3	9
125	Recent advances in atomic-scale spin-polarized scanning tunneling microscopy. *Microscopy Research and Technique*, **2005**, 66, 72-84	2.8	7
124	Crystal structure, electronic structure and magnetism of transition metal nitrides. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 2516-2519		14
123	First-principles study of the structural and magnetic properties of iron indium nitride. *Journal of Applied Physics*, **2005**, 97, 10D309	2.5	3

122	Electronic structure and magnetic properties of Mn3GaN precipitates in Ga1−xMnxN. *Physical Review B*, **2005**, 72,	3.3	18
121	Theoretical study of cation-related point defects in ZnGeP2. *Physical Review B*, **2005**, 71,	3.3	23
120	Stability and half-metallicity of transition metal pnictides in tetrahedrally bonded structures. *Physical Review B*, **2005**, 71,	3.3	37
119	Universal transition state for high-pressure zinc blende to rocksalt phase transitions. *Physical Review Letters*, **2005**, 94, 225501	7.4	64
118	Structure and phonons of ZnGeN2. *Physical Review B*, **2005**, 72,	3.3	36
117	The effects of biaxial strain on stability and half-metallicity of zinc blende CrSb. *Journal of Applied Physics*, **2005**, 97, 10C304	2.5	5
116	Effects of biaxial strain on stability and half-metallicity of Cr and Mn pnictides and chalcogenides in the zinc-blende structure. *Physical Review B*, **2005**, 72,	3.3	28
115	Noncritically phase-matched second-harmonic-generation chalcopyrites based on CdSiAs2 and CdSiP2. *Physical Review B*, **2004**, 70,	3.3	25
114	Electronic band structure of ordered vacancy defect chalcopyrite compounds with formula II□I2▽I4. *Physical Review B*, **2004**, 69,	3.3	79
113	First-principles study of the preference for zinc-blende or rocksalt structures in FeN and CoN. *Physical Review B*, **2004**, 70,	3.3	56
112	First-principles calculations of second-order optical response functions in chalcopyrite semiconductors. *Journal of Physics and Chemistry of Solids*, **2003**, 64, 1615-1619	3.9	17
111	Electronic structure of thin heterocrystalline superlattices in SiC and AlN. *Physical Review B*, **2003**, 68,	3.3	19
110	Magnetic properties of substitutional 3d transition metal impurities in silicon carbide. *Physical Review B*, **2003**, 68,	3.3	71
109	Electronic Structure of Native Point Defects in ZnGeP2. *Materials Research Society Symposia Proceedings*, **2003**, 799, 203		
108	Unified path for high-pressure transitions of SiC polytypes to the rocksalt structure. *Physical Review B*, **2003**, 68,	3.3	49
107	Electronic structure and magnetic interactions in MnN and Mn3N2. *Physical Review B*, **2003**, 68,	3.3	55
106	Anisotropy of UV-reflectivity in wurtzite crystals: a comparison between GaN and CdSe. *Solid State Communications*, **2002**, 121, 549-554	1.6	10
105	Atomic-scale spin-polarized scanning tunneling microscopy applied to Mn3N2(010). *Physical Review Letters*, **2002**, 89, 226101	7.4	70

104	Band structure of CdGeAs2 near the fundamental gap. *Physical Review B*, **2002**, 65,	3.3	24
103	Changes of the geometry and band structure of SiC along the orthorhombic high-pressure transition path between the zinc-blende and rocksalt structures. *Physical Review B*, **2002**, 66,	3.3	39
102	Pressure dependence of sound velocities in 3C□SiC and their relation to the high-pressure phase transition. *Physical Review B*, **2002**, 66,	3.3	37
101	Comment on "Orthorhombic Intermediate State in the Zinc Blende to Rocksalt Transformation Path of SiC at High Pressure". *Physical Review Letters*, **2002**, 88, 189601; discussion 189602	7.4	26
100	Valence-band ordering and magneto-optic exciton fine structure in ZnO. *Physical Review B*, **2002**, 65,	3.3	229
99	Homogeneous Strain Deformation Path for the Wurtzite to Rocksalt High-Pressure Phase Transition in GaN. *Physical Review Letters*, **2001**, 86, 91-94	7.4	131
98	Stacking fault band structure in 4H□SiC and its impact on electronic devices. *Applied Physics Letters*, **2001**, 79, 4360-4362	3.4	149
97	Theoretical study of the relative stability of wurtzite and rocksalt phases in MgO and GaN. *Physical Review B*, **2001**, 63,	3.3	152
96	Second-harmonic generation of I-III-VI2 chalcopyrite semiconductors: Effects of chemical substitutions. *Physical Review B*, **2001**, 63,	3.3	212
95	Electronic Structure and Magnetic Properties of Transition Metal Doped Silicon Carbide. *Materials Research Society Symposia Proceedings*, **2001**, 690, F6.8.1		
94	Identification of Raman-active phonon modes in oriented platelets of InN and polycrystalline InN. *Solid State Communications*, **2000**, 114, 355-360	1.6	30
93	Strong enhancement of second-order response coefficients in tellurium containing AgⅢⅣVI2 compounds. *Applied Physics Letters*, **2000**, 77, 190-192	3.4	19
92	Theory of Below Gap Absorption Bands in n-Type SiC Polytypes; Or, how SiC got its Colors. *Materials Science Forum*, **2000**, 338-342, 545-550	0.4	2
91	Electronic structure and optical spectra of the semimetal ScAs and of the indirect-band-gap semiconductors ScN and GdN. *Physical Review B*, **2000**, 62, 13538-13545	3.3	148
90	Theoretical Studies of ZnO and Related MgxZn1□O Alloy Band Structures. *MRS Internet Journal of Nitride Semiconductor Research*, **1999**, 4, 582-587		4
89	High field electron transport properties of bulk ZnO. *Journal of Applied Physics*, **1999**, 86, 6864-6867	2.5	138
88	Electronic structure of ZnGeP2: A detailed study of the band structure near the fundamental gap and its associated parameters. *Physical Review B*, **1999**, 60, 8087-8096	3.3	35
87	Optical-absorption bands in the 1□ eV range in n-type SiC polytypes. *Physical Review B*, **1999**, 59, 12890-12899	3.3	51

86	First-Principles Calculations of Nonlinear Optical Response Functions in Semiconductors. *Materials Research Society Symposia Proceedings*, **1999**, 579, 137		
85	Electronic Structure and Derived Linear and Nonlinear Optical Properties of Chalcopyrites. *Materials Research Society Symposia Proceedings*, **1999**, 607, 385		
84	Second-harmonic generation and birefringence of some ternary pnictide semiconductors. *Physical Review B*, **1999**, 59, 2737-2748	3.3	80
83	Theoretical evaluation of LiGaO_2 for frequency upconversion to ultraviolet. *Journal of the Optical Society of America B: Optical Physics*, **1999**, 16, 2217	1.7	17
82	Electronic Structure and Optical Properties of ZnGeN2. *MRS Internet Journal of Nitride Semiconductor Research*, **1999**, 4, 600-605		11
81	Nanometer-scale investigation of metal-SiC interfaces using ballistic electron emission microscopy. *Journal of Electronic Materials*, **1998**, 27, 345-352	1.9	13
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